

Silicon NPN Power Transistors

BDX67B

DESCRIPTION

- With TO-3 package
- High current capability
- DARLINGTON

APPLICATIONS

- Designed for power amplification and switching application.

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

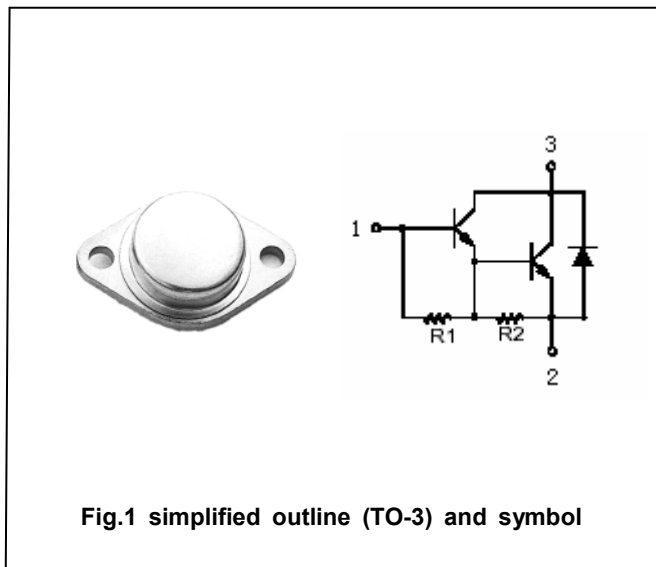


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	120	V
V _{CEO}	Collector-emitter voltage	Open base	100	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		16	A
I _{CM}	Collector current(peak)		20	A
I _B	Base current		0.25	A
P _T	Total power dissipation	T _C =25°C	117	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~200	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.17	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0; L=25mH	100			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10A ; I _B =0.04A			2	V
I _{CBO}	Collector cut-off current	V _{CB} =60V; I _E =0 T _C =150°C			1 5	mA
I _{CEO}	Collector cut-off current	V _{CE} =50V; I _B =0			3	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			3	mA

Switching times

t _{on}	Turn-on time	I _C =-10A ; I _{B1} =-I _{B2} =0.04A V _{CC} =12V ;		1.0		μs
t _{off}	Turn-off time			3.5		μs

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PACKAGE OUTLINE

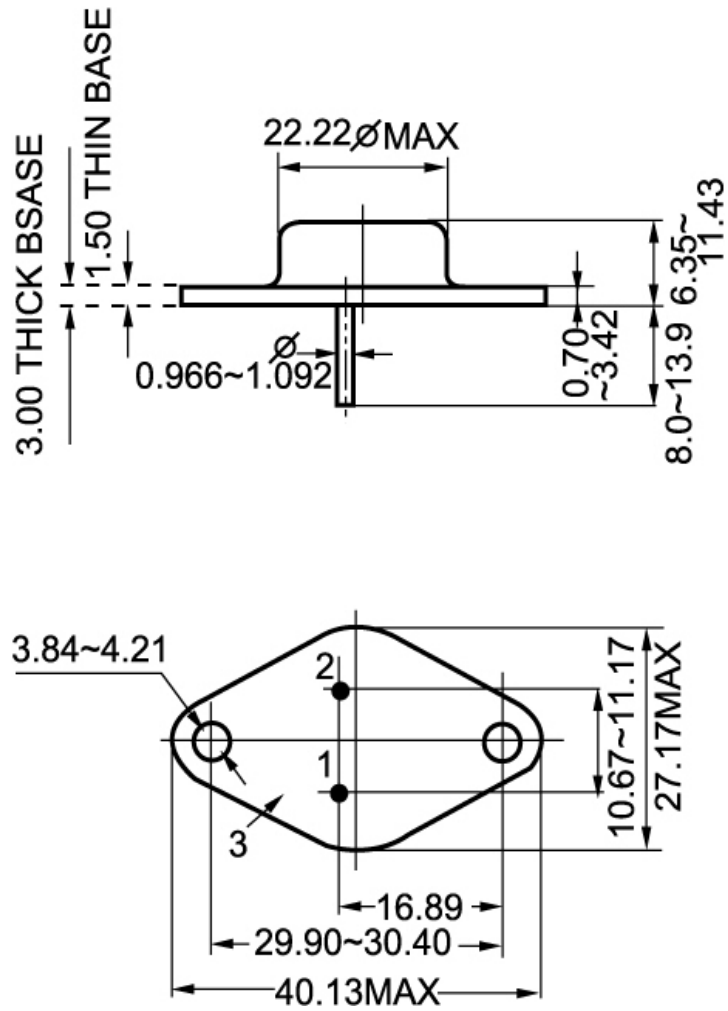


Fig.2 Outline dimensions